HC3M0015065D

SiC Power MOSFET N-Channel Enhancement Mode

Features

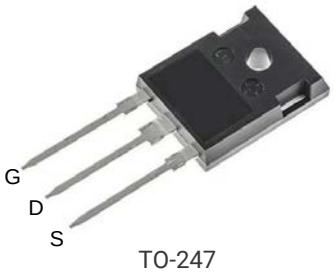
- 3rd Generation SiC MOSFET technology
- High blocking voltage with low on-resistance
- High speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Qrr)
- Halogen free, RoHS compliant

Benefits

- Higher system efficiency
- Reduced cooling requirements
- Increased power density
- Increased system switching frequency

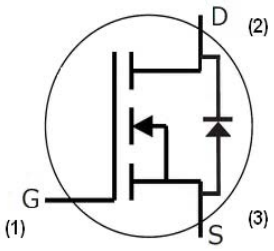
Applications

- Solar inverters
- EV motor drive
- High voltage DC/DC converters
- Switched mode power supplies



TO-247

Package



Part Number	Package	Marking
HC3M0015065D	TO-247	HC3M0015065D

Maximum Ratings (T_C = 25 ˚C unless otherwise specified)

Symbol	Parameter	Value	Unit	Note
V_{DSmax}	Drain - Source Voltage	650	V	
V_{GSmax}	Gate - Source voltage	-8/+19	V	Note 1
I_D	Continuous Drain Current, V_{GS} = 15 V, T_C = 25˚C	120	A	Fig. 19 Note 2
	Continuous Drain Current, V_{GS} = 15 V, T_C = 100˚C	96		
$I_{D(pulse)}$	Pulsed Drain Current, Pulse width t_P limited by T_{jmax}	418	A	
P_D	Power Dissipation, T_C=25˚C, T_J = 175 ˚C	416	W	Fig. 20
T_J , T_{stg}	Operating Junction and Storage Temperature	-40 to +175	˚C	
T_L	Solder Temperature, 1.6mm (0.063") from case for 10s	260	˚C	
M_d	Mounting Torque, (M3 or 6-32 screw)	1 8.8	Nm lbf-in	

Note (1): Recommended turn off / turn on gate voltage V_{GS} - 4V...0V / +15V
Note (2): Package limited to 120 A

Electrical Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	650			V	V_{GS} = 0 V, I_D = 100 µA	
$V_{GS(th)}$	Gate Threshold Voltage	1.8	2.3	3.6	V	V_{DS} = V_{GS}, I_D = 15.5 mA	Fig. 11
			1.9		V	V_{DS} = V_{GS}, I_D = 15.5 mA, T_J = 175ºC	
I_{DSS}	Zero Gate Voltage Drain Current		1	50	µA	V_{DS} = 650 V, V_{GS} = 0 V	
I_{GSS}	Gate-Source Leakage Current		10	250	nA	V_{GS} = 15 V, V_{DS} = 0 V	
$R_{DS(on)}$	Drain-Source On-State Resistance	10.5	15	21	mΩ	V_{GS} = 15 V, I_D = 55.8A	Fig. 4, 5,6
			20			V_{GS} = 15 V, I_D = 55.8A, T_J = 175ºC	
g_{fs}	Transconductance		42		S	V_{DS}= 20 V, I_{DS}= 55.8 A	Fig. 7
			40			V_{DS}= 20 V, I_{DS}= 55.8 A, T_J = 175ºC	
C_{iss}	Input Capacitance		5011		pF	V_{GS} = 0 V, V_{DS} = 400 V f = 100 Khz V_{AC} = 25 mV	Fig. 17, 18
C_{oss}	Output Capacitance		289				
C_{rss}	Reverse Transfer Capacitance		31				
$C_{o(er)}$	Effective Output Capacitance (Energy Related)		357				Note: 3
$C_{o(tr)}$	Effective Output Capacitance (Time Related)		516				Note: 3
E_{oss}	C_{oss} Stored Energy		29		µJ		Fig. 16
E_{ON}	Turn-On Switching Energy (Body Diode)		1500		µJ	V_{DS} = 400 V, V_{GS} = -4 V/15 V, I_D = 55.8 A, $R_{G(ext)}$ = 5 Ω, L= 57.6 µH, T_J = 175ºC FWD = Internal Body Diode of MOSFET	Fig. 25
E_{OFF}	Turn Off Switching Energy (Body Diode)		700				
E_{ON}	Turn-On Switching Energy (External Diode)		1200		µJ	V_{DS} = 400 V, V_{GS} = -4 V/15 V, I_D = 55.8 A, $R_{G(ext)}$ = 5 Ω, L= 57.6 µH, T_J = 175ºC FWD = External SiC DIODE	Fig. 25
E_{OFF}	Turn Off Switching Energy (External Diode)		1000				
$t_{d(on)}$	Turn-On Delay Time		22		ns	V_{DD} = 400 V, V_{GS} = -4 V/15 V I_D = 55.8 A, $R_{G(ext)}$ = 5 Ω, L= 57.6 µH Timing relative to V_{DS} Inductive load	Fig. 26
t_r	Rise Time		125				
$t_{d(off)}$	Turn-Off Delay Time		58				
t_f	Fall Time		25				
$R_{G(int)}$	Internal Gate Resistance		1.5		Ω	f = 1 MHz, V_{AC} = 25 mV	
Q_{gs}	Gate to Source Charge		54		nC	V_{DS} = 400 V, V_{GS} = -4 V/15 V I_D = 55.8 A Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		62				
Q_g	Total Gate Charge		188				

Note (3): $C_{o(er)}$, a lumped capacitance that gives same stored energy as Coss while Vds is rising from 0 to 400V
$C_{o(tr)}$, a lumped capacitance that gives same charging time as Coss while Vds is rising from 0 to 400V

Reverse Diode Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	4.7		V	V_{GS} = -4 V, I_{SD} = 27.9 A, T_J = 25 °C	Fig. 8, 9, 10
		4.2		V	V_{GS} = -4 V, I_{SD} = 27.9 A, T_J = 175 °C	
I_S	Continuous Diode Forward Current		79	A	V_{GS} = -4 V, T_C = 25˚C	
$I_{S,pulse}$	Diode pulse Current		418	A	V_{GS} = -4 V, pulse width t_P limited by T_{jmax}	
t_{rr}	Reverse Recovery time	85		ns	V_{GS} = -4 V, I_{SD} = 55.8 A, V_R = 400 V dif/dt = 1500 A/µs, T_J = 175 °C	
Q_{rr}	Reverse Recovery Charge	667		nC		
I_{rrm}	Peak Reverse Recovery Current	17		A		
t_{rr}	Reverse Recovery time	74		ns	V_{GS} = -4 V, I_{SD} = 55.8 A, V_R = 400 V dif/dt = 1000 A/µs, T_J = 175 °C	
Q_{rr}	Reverse Recovery Charge	562		nC		
I_{rrm}	Peak Reverse Recovery Current	14		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.35	°C/W		Fig. 21
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient	40			

Typical Performance

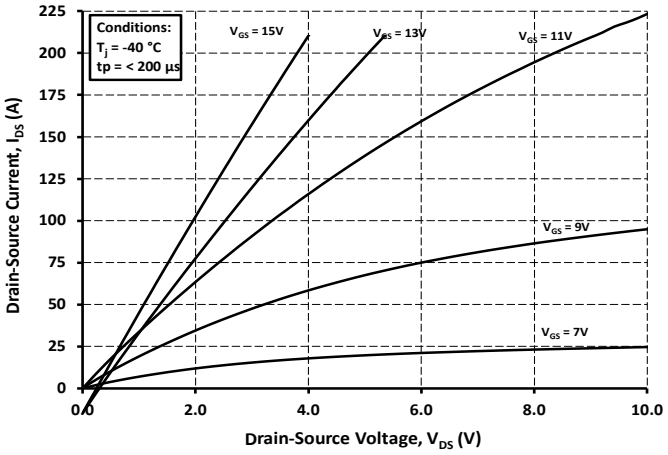


Figure 1. Output Characteristics T_J = -40 °C

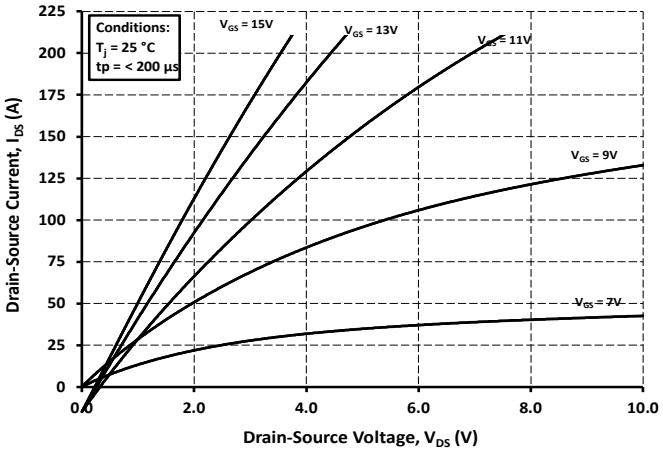


Figure 2. Output Characteristics T_J = 25 °C

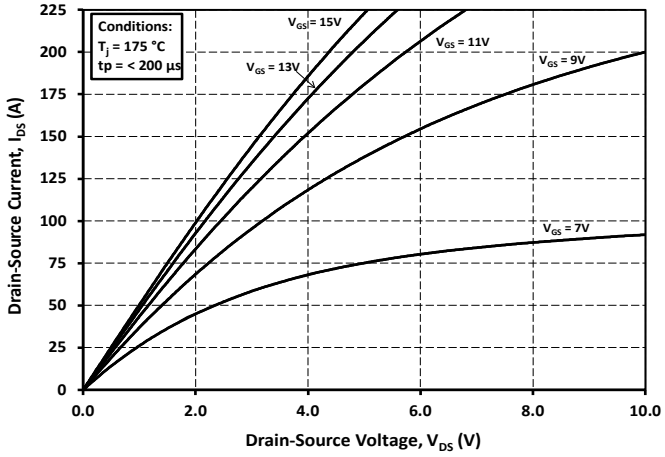


Figure 3. Output Characteristics T_J = 175 °C

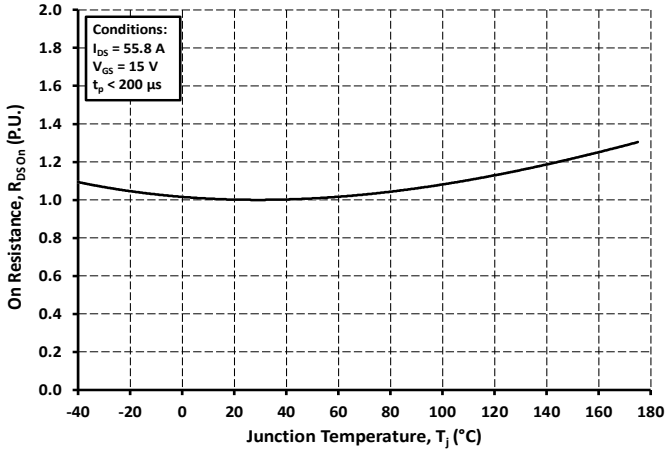


Figure 4. Normalized On-Resistance vs. Temperature

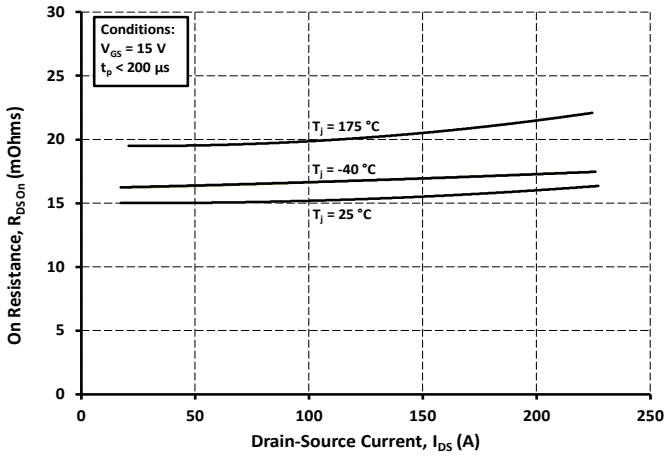


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

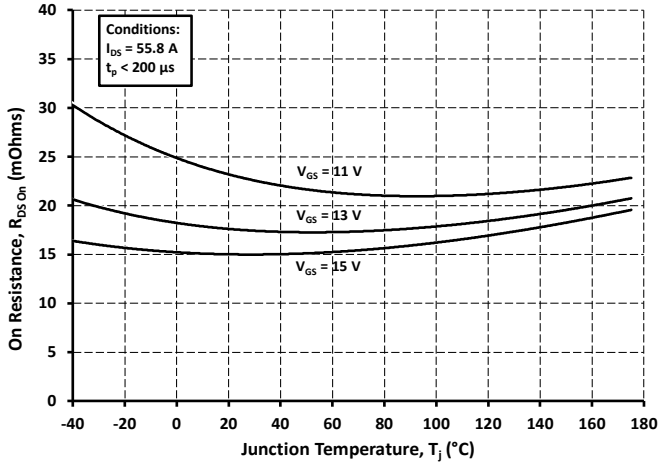


Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

Typical Performance

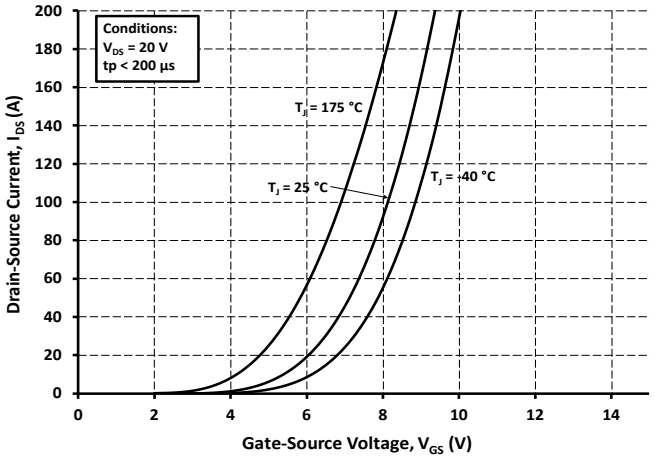


Figure 7. Transfer Characteristic for Various Junction Temperatures

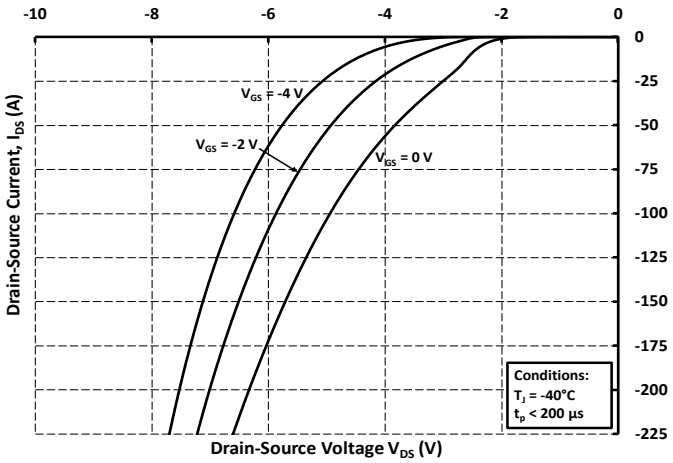


Figure 8. Body Diode Characteristic at -40 °C

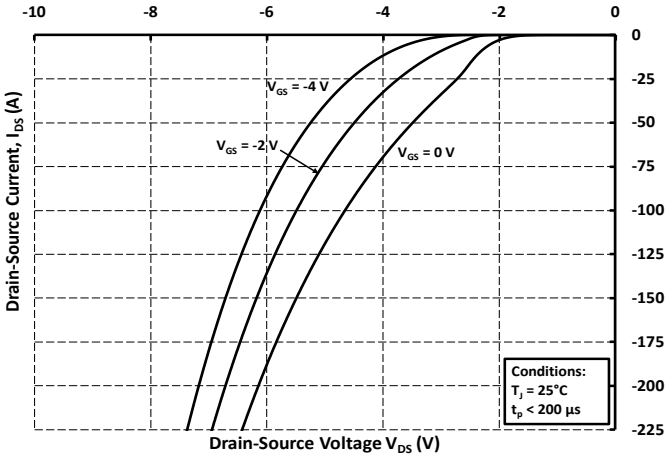


Figure 9. Body Diode Characteristic at 25 °C

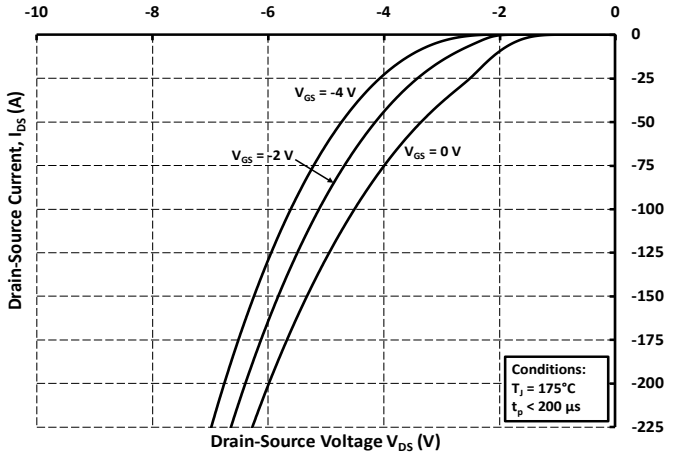


Figure 10. Body Diode Characteristic at 175 °C

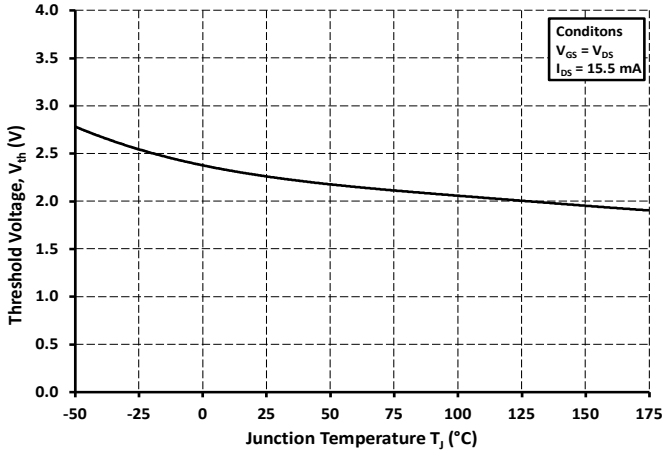


Figure 11. Threshold Voltage vs. Temperature

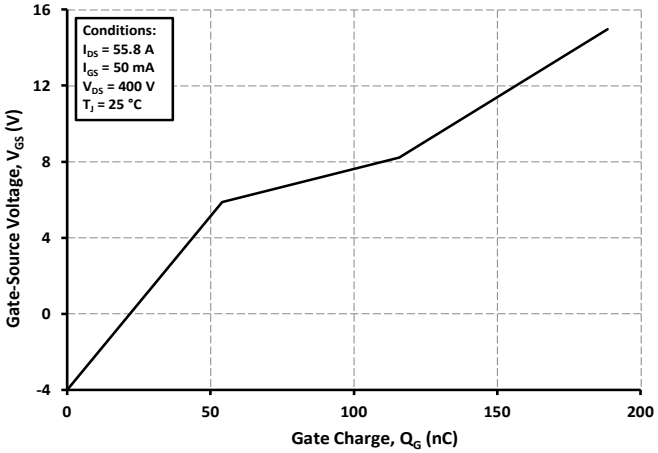


Figure 12. Gate Charge Characteristics

Typical Performance

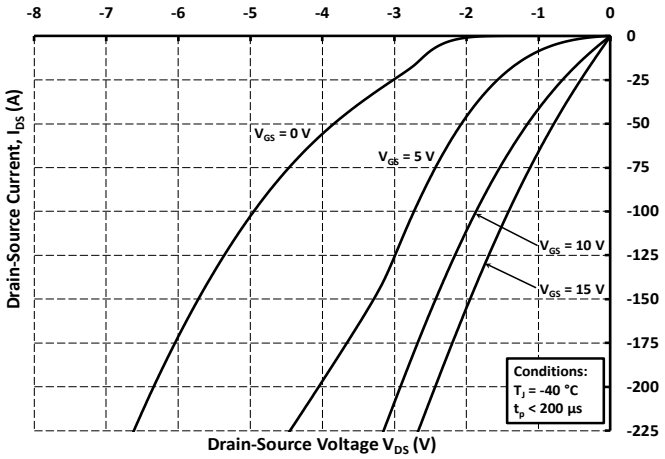


Figure 13. 3rd Quadrant Characteristic at -40 °C

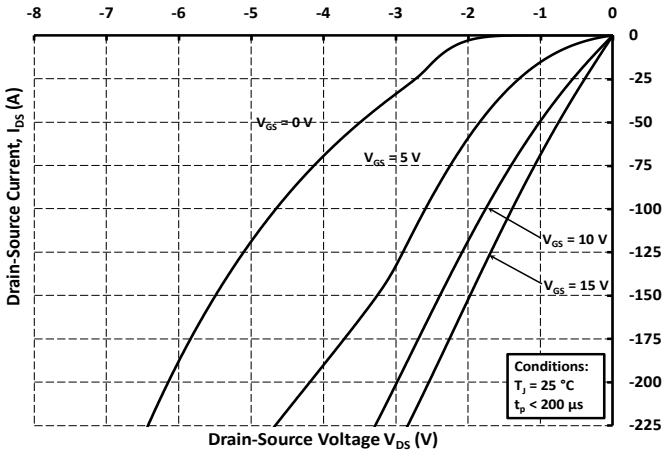


Figure 14. 3rd Quadrant Characteristic at 25 °C

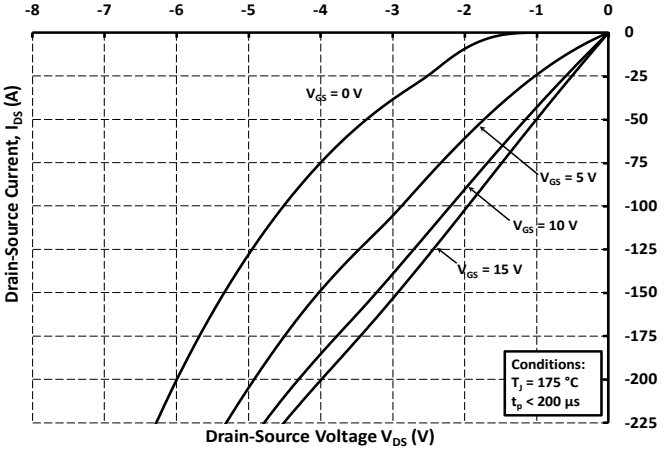


Figure 15. 3rd Quadrant Characteristic at 175 °C

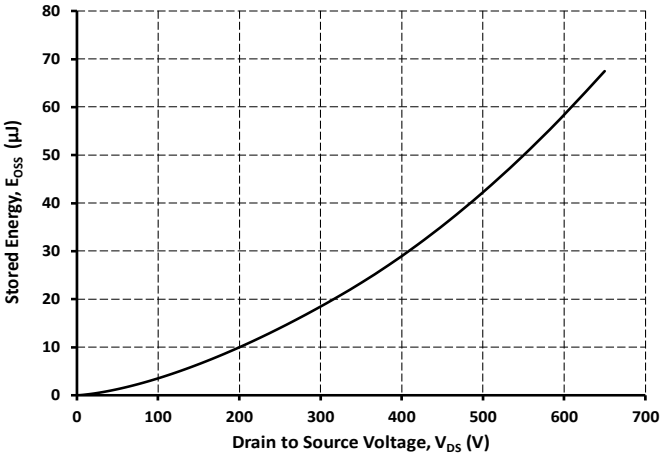


Figure 16. Output Capacitor Stored Energy

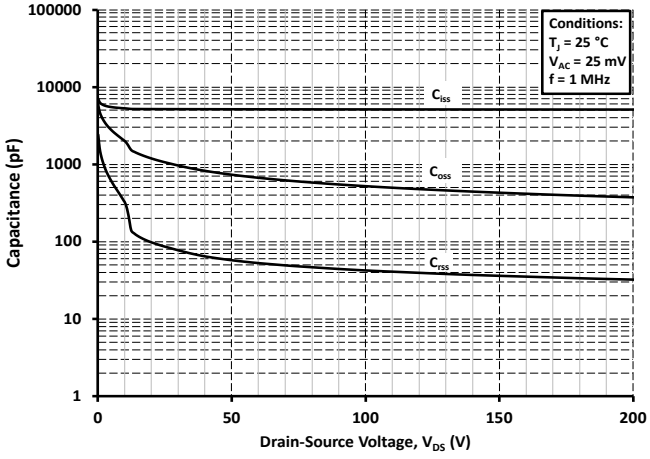


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

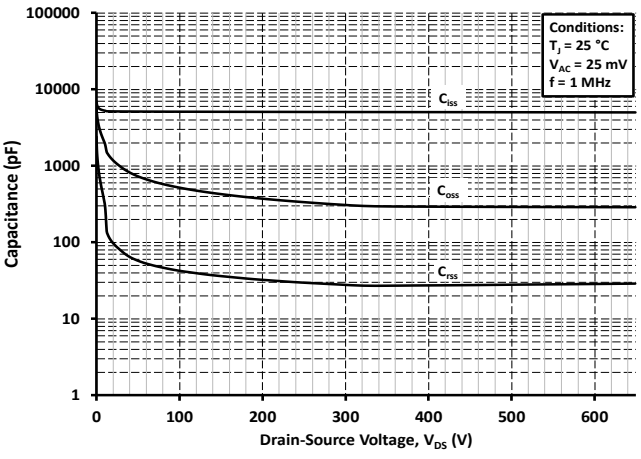


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 650V)

Typical Performance

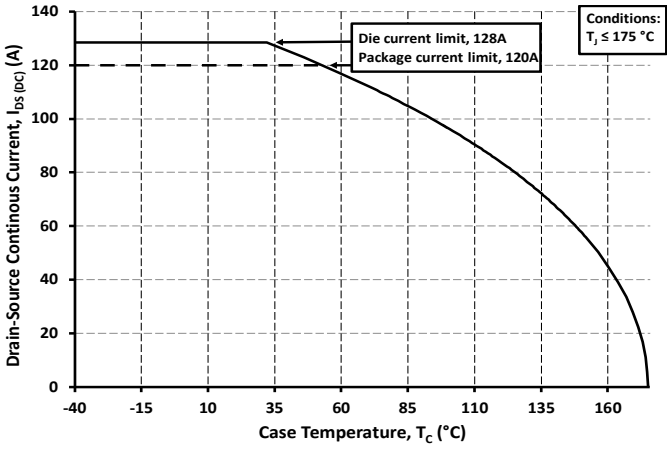


Figure 19. Continuous Drain Current Derating vs. Case Temperature

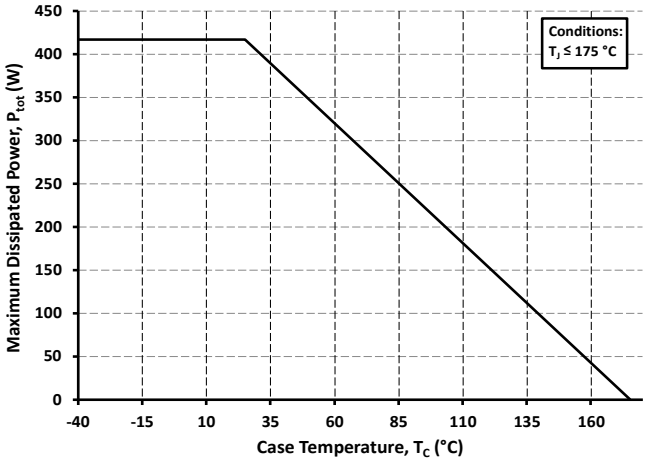


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

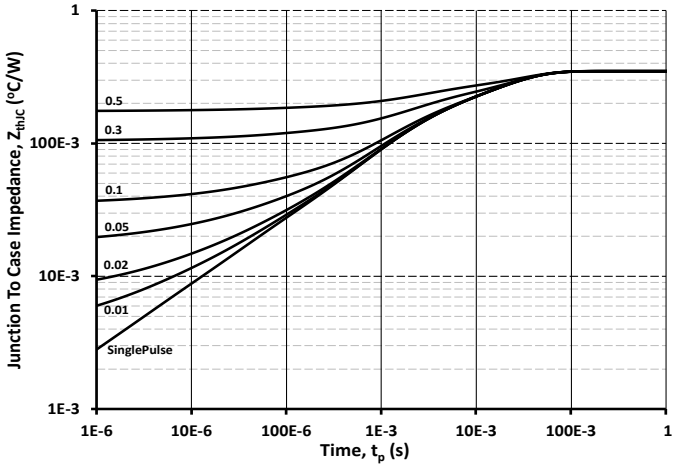


Figure 21. Transient Thermal Impedance (Junction - Case)

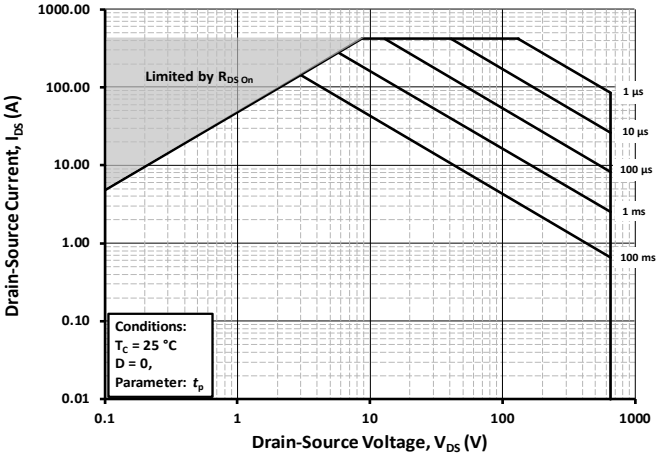


Figure 22. Safe Operating Area

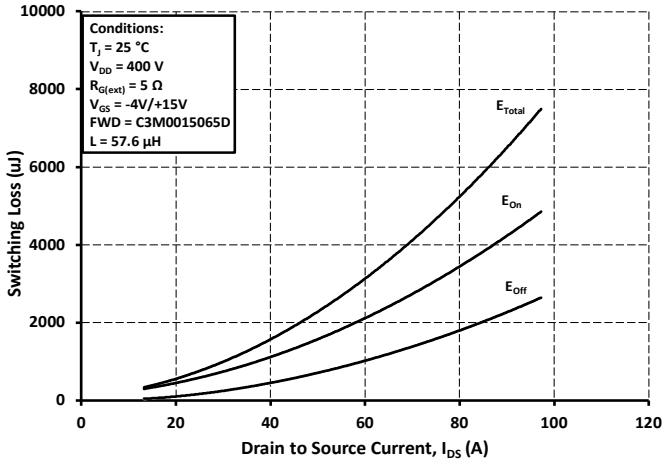


Figure 23. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 400V)

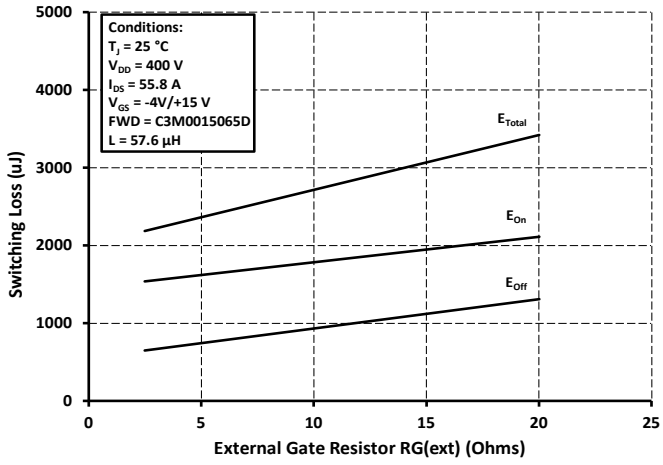


Figure 24. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

Typical Performance

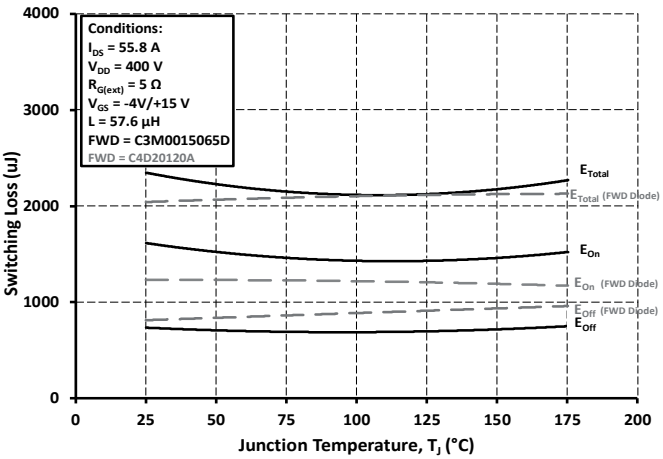


Figure 25. Clamped Inductive Switching Energy vs. Temperature

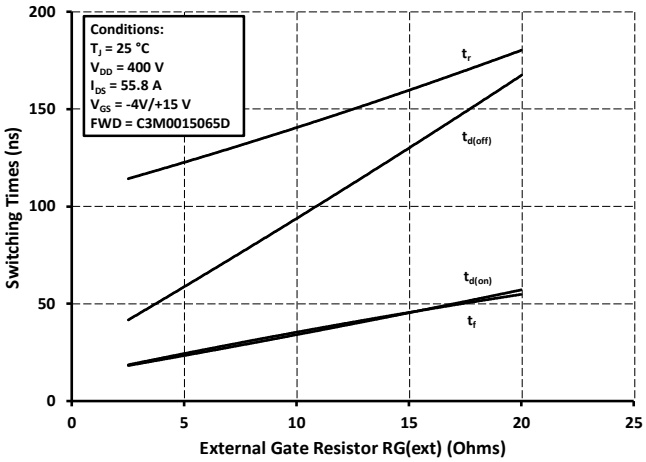


Figure 26. Switching Times vs. $R_{G(ext)}$

Test Circuit Schematic

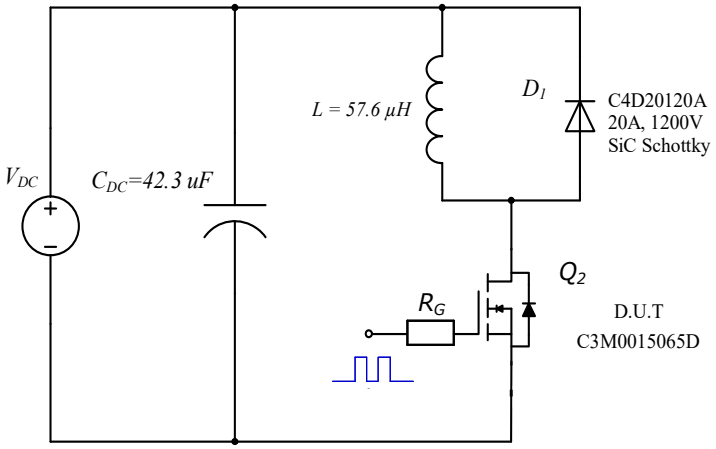


Figure 27. Clamped Inductive Switching Waveform Test Circuit

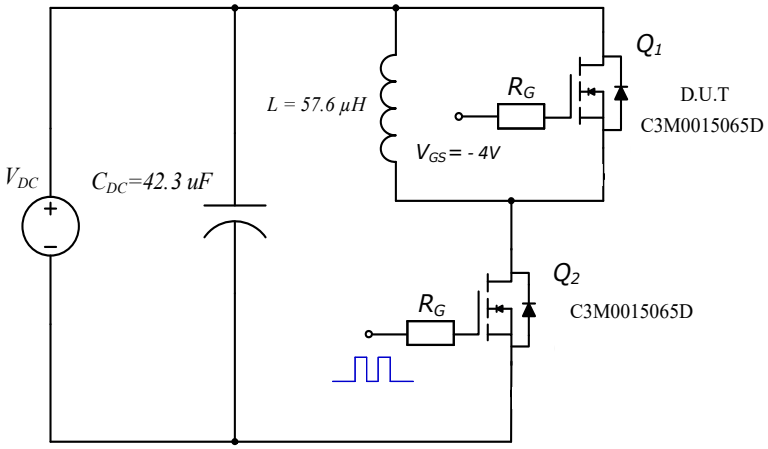


Figure 28. Body Diode Recovery Test Circuit

Package Dimensions

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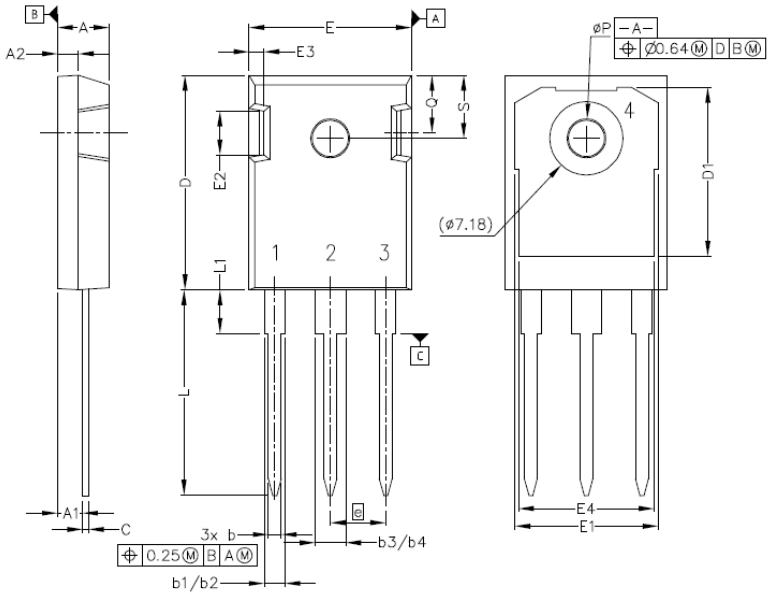
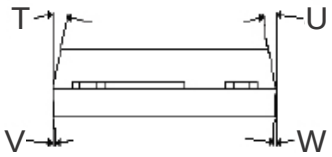


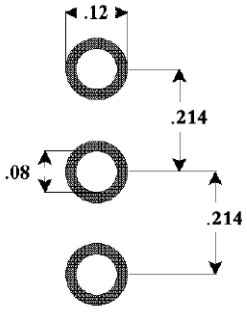


Pinout Information:

- Pin 1 = Gate
- Pin 2, 4 = Drain
- Pin 3 = Source

POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.042	.052	1.07	1.33
b1	.075	.095	1.91	2.41
b2	.075	.085	1.91	2.16
b3	.113	.133	2.87	3.38
b4	.113	.123	2.87	3.13
c	.022	.027	0.55	0.68
D	.819	.831	20.80	21.10
D1	.640	.695	16.25	17.65
D2	.037	.049	0.95	1.25
E	.620	.635	15.75	16.13
E1	.516	.557	13.10	14.15
E2	.145	.201	3.68	5.10
E3	.039	.075	1.00	1.90
E4	.487	.529	12.38	13.43
e	.214 BSC		5.44 BSC	
N	3		3	
L	.780	.800	19.81	20.32
L1	.161	.173	4.10	4.40
ØP	.138	.144	3.51	3.65
Q	.216	.236	5.49	6.00
S	.238	.248	6.04	6.30
T	9°	11°	9°	11°
U	9°	11°	9°	11°
V	2°	8°	2°	8°
W	2°	8°	2°	8°

Recommended Solder Pad Layout



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